

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED MESA TYPE

2SC5587

HORIZONTAL DEFLECTION OUTPUT FOR SUPER HIGH RESOLUTION DISPLAY, COLOR TV

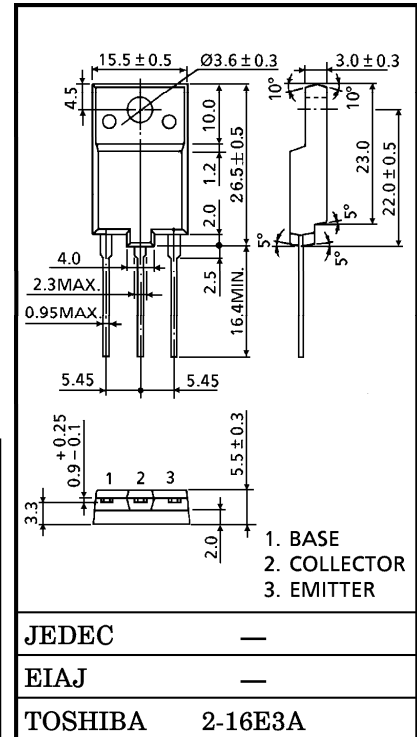
HIGH SPEED SWITCHING APPLICATIONS

- High Voltage : $V_{CBO} = 1500\text{ V}$
- Low Saturation Voltage : $V_{CE(sat)} = 3\text{ V (Max.)}$
- High Speed : $t_f(2) = 0.1\ \mu\text{s (Typ.)}$

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	1500	V
Collector-Emitter Voltage	V_{CEO}	750	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	DC	I_C	17
	Pulse	I_{CP}	34
Base Current	I_B	8.5	A
Collector Power Dissipation ($T_c = 25^\circ\text{C}$)	P_C	75	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$

Unit in mm



JEDEC	—
EIAJ	—
TOSHIBA	2-16E3A

Weight : 5.5 g (Typ.)

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Collector Cut-off Current	I_{CBO}	$V_{CB} = 1500\text{ V}, I_E = 0$	—	—	1	mA	
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 5\text{ V}, I_C = 0$	—	—	100	μA	
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10\text{ mA}, I_B = 0$	750	—	—	V	
DC Current Gain	$h_{FE(1)}$	$V_{CE} = 5\text{ V}, I_C = 2\text{ A}$	22	—	48	—	
	$h_{FE(2)}$	$V_{CE} = 5\text{ V}, I_C = 7\text{ A}$	9	—	18		
	$h_{FE(3)}$	$V_{CE} = 5\text{ V}, I_C = 14\text{ A}$	5	—	8		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 14\text{ A}, I_B = 3.5\text{ A}$	—	—	3	V	
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 14\text{ A}, I_B = 3.5\text{ A}$	—	1.0	1.5	V	
Transition Frequency	f_T	$V_{CE} = 10\text{ V}, I_C = 0.1\text{ A}$	—	2	—	MHz	
Collector Output Capacitance	C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	240	—	pF	
Switching Time	Storage Time	$t_{stg(1)}$	$I_{CP} = 9\text{ A}, I_{B1}(\text{end}) = 1.3\text{ A}$	—	2.7	3	μs
	Fall Time	$t_f(1)$	$f_H = 64\text{ kHz}$	—	0.2	0.3	
	Storage Time	$t_{stg(2)}$	$I_{CP} = 7.5\text{ A}, I_{B1}(\text{end}) = 1.1\text{ A}$	—	1.8	2	μs
	Fall Time	$t_f(2)$	$f_H = 100\text{ kHz}$	—	0.1	0.15	

